

# 74HC245; 74HCT245

Octal bus transceiver; 3-state

Rev. 03 — 31 January 2005

Product data sheet

## 1. General description

The 74HC245; 74HCT245 is a high-speed Si-gate CMOS device and is pin compatible with Low-Power Schottky TTL (LSTTL).

The 74HC245; 74HCT245 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The 74HC245; 74HCT245 features an output enable input ( $\overline{OE}$ ) for easy cascading and a send/receive input (DIR) for direction control.  $\overline{OE}$  controls the outputs so that the buses are effectively isolated.

The 74HC245; 74HCT245 is similar to the 74HC640; 74HCT640 but has true (non-inverting) outputs.

## 2. Features

- Octal bidirectional bus interface
- Non-inverting 3-state outputs
- Multiple package options
- Complies with JEDEC standard no. 7A
- ESD protection:
  - ◆ HBM EIA/JESD22-A114-B exceeds 2000 V
  - ◆ MM EIA/JESD22-A115-A exceeds 200 V
- Specified from  $-40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$  and from  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$

勝特力材料 886-3-5753170  
胜特力电子(上海) 86-21-54151736  
胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

## 3. Quick reference data

Table 1: Quick reference data

$GND = 0\text{ V}$ ;  $T_{amb} = 25^{\circ}\text{C}$ ;  $t_r = t_f = 6\text{ ns}$ .

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Type 74HC245</b>						
$t_{PHL}, t_{PLH}$	propagation delay An to Bn or Bn to An	$C_L = 15\text{ pF};$ $V_{CC} = 5\text{ V}$	-	7	-	ns
$C_I$	input capacitance		-	3.5	-	pF
$C_{I/O}$	input/output capacitance		-	10	-	pF
$C_{PD}$	power dissipation capacitance per transceiver	$V_I = \text{GND to } V_{CC}$	[1]	-	30	pF
<b>Type 74HCT245</b>						
$t_{PHL}, t_{PLH}$	propagation delay An to Bn or Bn to An	$C_L = 15\text{ pF};$ $V_{CC} = 5\text{ V}$	-	10	-	ns

PHILIPS

**Table 1: Quick reference data ...continued**  
 $GND = 0 \text{ V}$ ;  $T_{amb} = 25^\circ\text{C}$ ;  $t_r = t_f = 6 \text{ ns}$ .

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$C_I$	input capacitance		-	3.5	-	pF	
$C_{I/O}$	input/output capacitance		-	10	-	pF	
$C_{PD}$	power dissipation capacitance per transceiver	$V_I = \text{GND to}$ $V_{CC} - 1.5 \text{ V}$	[1]	-	30	-	pF

[1]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$$

where:

$f_i$  = input frequency in MHz;

$f_o$  = output frequency in MHz;

$C_L$  = output load capacitance in pF;

$V_{CC}$  = supply voltage in V;

$N$  = number of inputs switching;

$\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

勝特力材料 886-3-5753170

胜特力电子(上海) 86-21-54151736

胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

## 4. Ordering information

**Table 2: Ordering information**

Type number	Package				Version
	Temperature range	Name	Description	Version	
74HC245N	−40 °C to +125 °C	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1	
74HC245D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1	
74HC245PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1	
74HC245DB	−40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1	
74HC245BQ	−40 °C to +125 °C	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1	
74HCT245N	−40 °C to +125 °C	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1	
74HCT245D	−40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1	
74HCT245PW	−40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1	
74HCT245DB	−40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1	
74HCT245BQ	−40 °C to +125 °C	DHVQFN20	plastic dual-in-line compatible thermal enhanced very thin quad flat package no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1	

## 5. Functional diagram

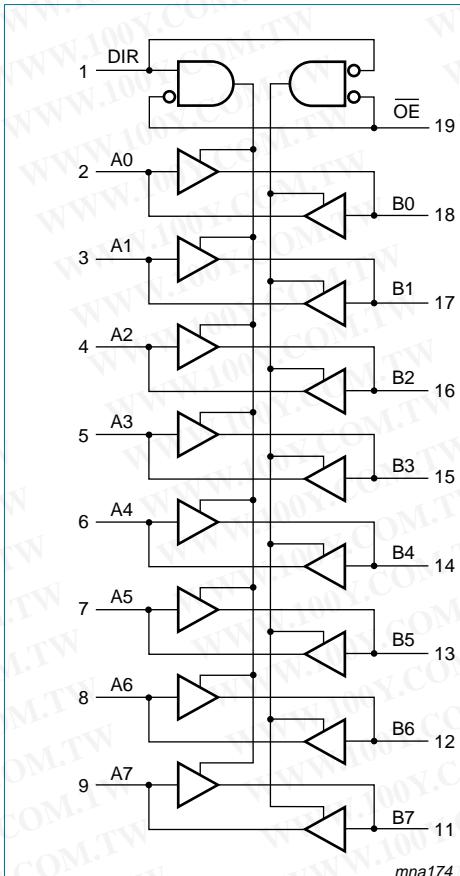


Fig 1. Logic symbol

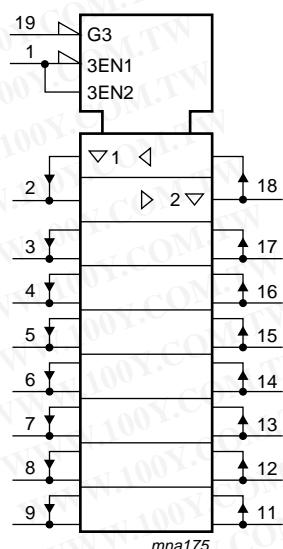


Fig 2. IEC logic symbol

勝特力材料 886-3-5753170  
胜特力电子(上海) 86-21-54151736  
胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

## 6. Pinning information

### 6.1 Pinning

<p><b>Fig 3. Pin configuration DIP20, SO20, SSOP20 and TSSOP20</b></p>	<p><b>Fig 4. Pin configuration DHVQFN20</b></p>
<p>(1) The die substrate is attached to this pad using conductive die attach material. It can not be used as supply pin or input</p>	

### 6.2 Pin description

Table 3: Pin description

Symbol	Pin	Description
DIR	1	direction control
A0	2	data input/output
A1	3	data input/output
A2	4	data input/output
A3	5	data input/output
A4	6	data input/output
A5	7	data input/output
A6	8	data input/output
A7	9	data input/output
GND	10	ground (0 V)
B7	11	data input/output
B6	12	data input/output
B5	13	data input/output
B4	14	data input/output
B3	15	data input/output
B2	16	data input/output

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

**Table 3:** Pin description ...*continued*

Symbol	Pin	Description
B1	17	data input/output
B0	18	data input/output
OE	19	output enable input (active LOW)
V <sub>CC</sub>	20	supply voltage

## 7. Functional description

### 7.1 Function table

**Table 4:** Function table [1]

Input		Input/output	
OE	DIR	An	Bn
L	L	A = B	input
L	H	input	B = A
H	X	Z	Z

[1] H = HIGH voltage level;  
 L = LOW voltage level;  
 X = don't care;  
 Z = high-impedance OFF-state.

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

## 8. Limiting values

**Table 5:** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7	V
I <sub>IK</sub>	input diode current	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>OK</sub>	output diode current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	-	±20	mA
I <sub>O</sub>	output source or sink current	V <sub>O</sub> = -0.5 V to V <sub>CC</sub> + 0.5 V	-	±35	mA
I <sub>CC</sub> , I <sub>GND</sub>	V <sub>CC</sub> or GND current		-	±70	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation		[1]		
	DIP20 package		-	750	mW
	SO20, SSOP20, TSSOP20 and DHVQFN20 packages		-	500	mW

- [1] For DIP20 packages: above 70 °C, P<sub>tot</sub> derates linearly with 12 mW/K.  
 For SO20 packages: above 70 °C, P<sub>tot</sub> derates linearly with 8 mW/K.  
 For SSOP20 and TSSOP20 packages: above 60 °C, P<sub>tot</sub> derates linearly with 5.5 mW/K.  
 For DHVQFN20 packages: above 60 °C, P<sub>tot</sub> derates linearly with 4.5 mW/K.

## 9. Recommended operating conditions

Table 6: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Type 74HC245</b>						
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
t <sub>r</sub> , t <sub>f</sub>	input rise and fall times	V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	- - -	- 6.0 -	1000 500 400	ns ns ns
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C
<b>Type 74HCT245</b>						
V <sub>CC</sub>	supply voltage		4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	V
t <sub>r</sub> , t <sub>f</sub>	input rise and fall times	V <sub>CC</sub> = 4.5 V	-	6.0	500	ns
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C

## 10. Static characteristics

Table 7: Static characteristics type 74HC245

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -20 µA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	V
		I <sub>O</sub> = -20 µA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	V
		I <sub>O</sub> = -20 µA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	V
		I <sub>O</sub> = -6.0 mA; V <sub>CC</sub> = 4.5 V	3.98	4.32	-	V
		I <sub>O</sub> = -7.8 mA; V <sub>CC</sub> = 6.0 V	5.48	5.81	-	V

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

**Table 7: Static characteristics type 74HC245 ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	0	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	V
		$I_O = 6.0 mA; V_{CC} = 4.5 V$	-	0.15	0.26	V
$I_{LI}$	input leakage current	$I_O = 7.8 mA; V_{CC} = 6.0 V$	-	0.16	0.26	V
		$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	$\pm 0.1$	$\mu A$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	$\pm 0.5$	$\mu A$
$I_{CC}$	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0 A$ ; $V_{CC} = 6.0 V$	-	-	8.0	$\mu A$
$C_I$	input capacitance		-	3.5	-	pF
$C_{I/O}$	input/output capacitance		-	10	-	pF
<b><math>T_{amb} = -40^{\circ}\text{C}</math> to <math>+85^{\circ}\text{C}</math></b>						
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 2.0 V$	1.5	-	-	V
		$V_{CC} = 4.5 V$	3.15	-	-	V
		$V_{CC} = 6.0 V$	4.2	-	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 2.0 V$	-	-	0.5	V
		$V_{CC} = 4.5 V$	-	-	1.35	V
		$V_{CC} = 6.0 V$	-	-	1.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = -20 \mu A; V_{CC} = 2.0 V$	1.9	-	-	V
		$I_O = -20 \mu A; V_{CC} = 4.5 V$	4.4	-	-	V
		$I_O = -20 \mu A; V_{CC} = 6.0 V$	5.9	-	-	V
		$I_O = -6.0 mA; V_{CC} = 4.5 V$	3.84	-	-	V
		$I_O = -7.8 mA; V_{CC} = 6.0 V$	5.34	-	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = 20 \mu A; V_{CC} = 2.0 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	-	0.1	V
		$I_O = 6.0 mA; V_{CC} = 4.5 V$	-	-	0.33	V
$I_{LI}$	input leakage current	$I_O = 7.8 mA; V_{CC} = 6.0 V$	-	-	0.33	V
		$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	$\pm 1.0$	$\mu A$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	$\pm 5.0$	$\mu A$
$I_{CC}$	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0 A$ ; $V_{CC} = 6.0 V$	-	-	80	$\mu A$
<b><math>T_{amb} = -40^{\circ}\text{C}</math> to <math>+125^{\circ}\text{C}</math></b>						
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 2.0 V$	1.5	-	-	V
		$V_{CC} = 4.5 V$	3.15	-	-	V
		$V_{CC} = 6.0 V$	4.2	-	-	V

**Table 7: Static characteristics type 74HC245 ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{IL}$	LOW-level input voltage	$V_{CC} = 2.0 \text{ V}$	-	-	0.5	V
		$V_{CC} = 4.5 \text{ V}$	-	-	1.35	V
		$V_{CC} = 6.0 \text{ V}$	-	-	1.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$	-	-	-	V
		$I_O = -20 \mu\text{A}; V_{CC} = 2.0 \text{ V}$	1.9	-	-	V
		$I_O = -20 \mu\text{A}; V_{CC} = 4.5 \text{ V}$	4.4	-	-	V
		$I_O = -20 \mu\text{A}; V_{CC} = 6.0 \text{ V}$	5.9	-	-	V
		$I_O = -6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.7	-	-	V
		$I_O = -7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.2	-	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$	-	-	-	V
		$I_O = 20 \mu\text{A}; V_{CC} = 2.0 \text{ V}$	-	-	0.1	V
		$I_O = 20 \mu\text{A}; V_{CC} = 4.5 \text{ V}$	-	-	0.1	V
		$I_O = 20 \mu\text{A}; V_{CC} = 6.0 \text{ V}$	-	-	0.1	V
		$I_O = 6.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.4	V
		$I_O = 7.8 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	-	0.4	V
$I_{LI}$	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	$\pm 1.0$	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	$\pm 10.0$	$\mu\text{A}$
$I_{CC}$	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 6.0 \text{ V}$	-	-	160	$\mu\text{A}$

**Table 8: Static characteristics type 74HCT245**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = 25^\circ\text{C}$						
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$	2.0	1.6	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$	-	1.2	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$	-	-	-	V
		$I_O = -20 \mu\text{A}$	4.4	4.5	-	V
		$I_O = -6 \text{ mA}$	3.98	4.32	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$	-	-	-	V
		$I_O = 20 \mu\text{A}$	-	0	0.1	V
		$I_O = 6.0 \text{ mA}$	-	0.15	0.26	V
$I_{LI}$	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	$\pm 0.1$	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 5.5 \text{ V}$ ; $V_O = V_{CC}$ or GND per input pin; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$	-	-	$\pm 0.5$	$\mu\text{A}$
$I_{CC}$	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	8.0	$\mu\text{A}$

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

**Table 8: Static characteristics type 74HCT245 ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$\Delta I_{CC}$	additional quiescent supply current per input pin	$V_I = V_{CC} - 2.1 \text{ V}$ ; other inputs at $V_I = V_{CC}$ or GND; $V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$ ; $I_O = 0 \text{ A}$				
	An or Bn inputs		-	40	144	$\mu\text{A}$
	$\overline{OE}$ input		-	150	540	$\mu\text{A}$
	DIR input		-	90	324	$\mu\text{A}$
$C_I$	input capacitance		-	3.5	-	$\text{pF}$
$C_{I/O}$	input/output capacitance		-	10	-	$\text{pF}$
<b><math>T_{amb} = -40^\circ\text{C}</math> to <math>+85^\circ\text{C}</math></b>						
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$	2.0	-	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$	-	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$				
		$I_O = -20 \mu\text{A}$	4.4	-	-	V
		$I_O = -6 \text{ mA}$	3.84	-	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$				
		$I_O = 20 \mu\text{A}$	-	-	0.1	V
		$I_O = 6.0 \text{ mA}$	-	-	0.33	V
$I_{LI}$	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	$\pm 1.0$	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 5.5 \text{ V}$ ; $V_O = V_{CC}$ or GND per input pin; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$	-	-	$\pm 5.0$	$\mu\text{A}$
$I_{CC}$	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 5.5 \text{ V}$	-	-	80	$\mu\text{A}$
$\Delta I_{CC}$	additional quiescent supply current per input pin	$V_I = V_{CC} - 2.1 \text{ V}$ ; other inputs at $V_I = V_{CC}$ or GND; $V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$ ; $I_O = 0 \text{ A}$				
	An or Bn inputs		-	-	180	$\mu\text{A}$
	$\overline{OE}$ input		-	-	675	$\mu\text{A}$
	DIR input		-	-	405	$\mu\text{A}$
<b><math>T_{amb} = -40^\circ\text{C}</math> to <math>+125^\circ\text{C}</math></b>						
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$	2.0	-	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5 \text{ V}$ to $5.5 \text{ V}$	-	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$				
		$I_O = -20 \mu\text{A}$	4.4	-	-	V
		$I_O = -6 \text{ mA}$	3.7	-	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 4.5 \text{ V}$				
		$I_O = 20 \mu\text{A}$	-	-	0.1	V
		$I_O = 6.0 \text{ mA}$	-	-	0.4	V
$I_{LI}$	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	$\pm 1.0$	$\mu\text{A}$
$I_{OZ}$	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_{CC} = 5.5 \text{ V}$ ; $V_O = V_{CC}$ or GND per input pin; other inputs at $V_{CC}$ or GND; $I_O = 0 \text{ A}$	-	-	$\pm 10$	$\mu\text{A}$

**Table 8: Static characteristics type 74HCT245 ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I <sub>CC</sub>	quiescent supply current	V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	160	µA
ΔI <sub>CC</sub>	additional quiescent supply current per input pin	V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; other inputs at V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A				
	An or Bn inputs		-	-	196	µA
	OE input		-	-	735	µA
	DIR input		-	-	441	µA

## 11. Dynamic characteristics

**Table 9: Dynamic characteristics type 74HC245**GND = 0 V; test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
t <sub>PHL</sub> , t <sub>PLH</sub>	propagation delay An to Bn or Bn to An	see <a href="#">Figure 5</a> V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF V <sub>CC</sub> = 6.0 V	-	25	90	ns
t <sub>PZH</sub> , t <sub>PZL</sub>	3-state output enable time OE to An or OE to Bn	see <a href="#">Figure 6</a> V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	-	30	150	ns
t <sub>PHZ</sub> , t <sub>PLZ</sub>	3-state output disable time OE to An or OE to Bn	see <a href="#">Figure 6</a> V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	-	15	30	ns
t <sub>THL</sub> , t <sub>TLH</sub>	output transition time	see <a href="#">Figure 5</a> V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	-	12	26	ns
C <sub>PD</sub>	power dissipation capacitance per transceiver	V <sub>I</sub> = GND to V <sub>CC</sub>	[1]	-	30	-
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
t <sub>PHL</sub> , t <sub>PLH</sub>	propagation delay An to Bn or Bn to An	see <a href="#">Figure 5</a> V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	-	-	115	ns

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

**Table 9: Dynamic characteristics type 74HC245 ...continued**  
*GND = 0 V; test circuit see [Figure 7](#).*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{PZH}, t_{PZL}$	3-state output enable time $\overline{OE}$ to An or $\overline{OE}$ to $B_n$	see <a href="#">Figure 6</a>	-	-	190	ns
		$V_{CC} = 2.0 \text{ V}$	-	-	38	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	33	ns
$t_{PHZ}, t_{PLZ}$	3-state output disable time $\overline{OE}$ to An or $\overline{OE}$ to $B_n$	see <a href="#">Figure 6</a>	-	-	190	ns
		$V_{CC} = 2.0 \text{ V}$	-	-	38	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	33	ns
$t_{THL}, t_{TLH}$	output transition time	see <a href="#">Figure 5</a>	-	-	75	ns
		$V_{CC} = 2.0 \text{ V}$	-	-	15	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	13	ns
		<b><math>T_{amb} = -40 \text{ }^{\circ}\text{C to } +125 \text{ }^{\circ}\text{C}</math></b>	-	-	-	-
$t_{PHL}, t_{PLH}$	propagation delay An to $B_n$ or $B_n$ to An	see <a href="#">Figure 5</a>	-	-	135	ns
		$V_{CC} = 2.0 \text{ V}$	-	-	27	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	23	ns
$t_{PZH}, t_{PZL}$	3-state output enable time $\overline{OE}$ to An or OE to $B_n$	see <a href="#">Figure 6</a>	-	-	225	ns
		$V_{CC} = 2.0 \text{ V}$	-	-	45	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	38	ns
$t_{PHZ}, t_{PLZ}$	3-state output disable time $\overline{OE}$ to An or $\overline{OE}$ to $B_n$	see <a href="#">Figure 6</a>	-	-	225	ns
		$V_{CC} = 2.0 \text{ V}$	-	-	45	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	38	ns
$t_{THL}, t_{TLH}$	output transition time	see <a href="#">Figure 5</a>	-	-	90	ns
		$V_{CC} = 2.0 \text{ V}$	-	-	18	ns
		$V_{CC} = 6.0 \text{ V}$	-	-	15	ns

[1]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

$f_i$  = input frequency in MHz;

$f_o$  = output frequency in MHz;

$C_L$  = output load capacitance in pF;

$V_{CC}$  = supply voltage in V;

N = number of inputs switching;

$\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

**Table 10: Dynamic characteristics type 74HCT245**GND = 0 V; test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
t <sub>PHL</sub> , t <sub>PLH</sub>	propagation delay An to Bn or Bn to An	see <a href="#">Figure 5</a> V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 5.0 V; C <sub>L</sub> = 15 pF	-	12	22	ns
t <sub>PZH</sub> , t <sub>PZL</sub>	3-state output enable time $\overline{OE}$ to An or $\overline{OE}$ to Bn	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 6</a>	-	16	30	ns
t <sub>PHZ</sub> , t <sub>PLZ</sub>	3-state output disable time $\overline{OE}$ to An or $\overline{OE}$ to Bn	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 6</a>	-	16	30	ns
t <sub>THL</sub> , t <sub>TLH</sub>	output transition time	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 5</a>	-	5	12	ns
C <sub>PD</sub>	power dissipation capacitance per transceiver	V <sub>I</sub> = GND to V <sub>CC</sub> – 1.5 V	[1]	30	-	pF
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
t <sub>PHL</sub> , t <sub>PLH</sub>	propagation delay An to Bn or Bn to An	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 5</a>	-	-	28	ns
t <sub>PZH</sub> , t <sub>PZL</sub>	3-state output enable time $\overline{OE}$ to An or $\overline{OE}$ to Bn	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 6</a>	-	-	38	ns
t <sub>PHZ</sub> , t <sub>PLZ</sub>	3-state output disable time $\overline{OE}$ to An or $\overline{OE}$ to Bn	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 6</a>	-	-	38	ns
t <sub>THL</sub> , t <sub>TLH</sub>	output transition time	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 5</a>	-	-	15	ns
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
t <sub>PHL</sub> , t <sub>PLH</sub>	propagation delay An to Bn or Bn to An	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 5</a>	-	-	33	ns
t <sub>PZH</sub> , t <sub>PZL</sub>	3-state output enable time $\overline{OE}$ to An or $\overline{OE}$ to Bn	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 6</a>	-	-	45	ns
t <sub>PHZ</sub> , t <sub>PLZ</sub>	3-state output disable time $\overline{OE}$ to An or $\overline{OE}$ to Bn	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 6</a>	-	-	45	ns
t <sub>THL</sub> , t <sub>TLH</sub>	output transition time	V <sub>CC</sub> = 4.5 V; see <a href="#">Figure 5</a>	-	-	18	ns

[1] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W):

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f<sub>i</sub> = input frequency in MHz;f<sub>o</sub> = output frequency in MHz;C<sub>L</sub> = output load capacitance in pF;V<sub>CC</sub> = supply voltage in V;

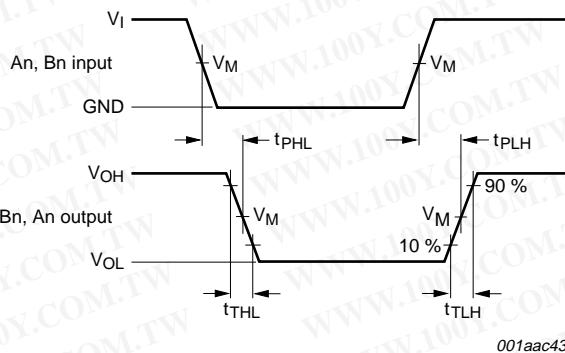
N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

## 12. Waveforms

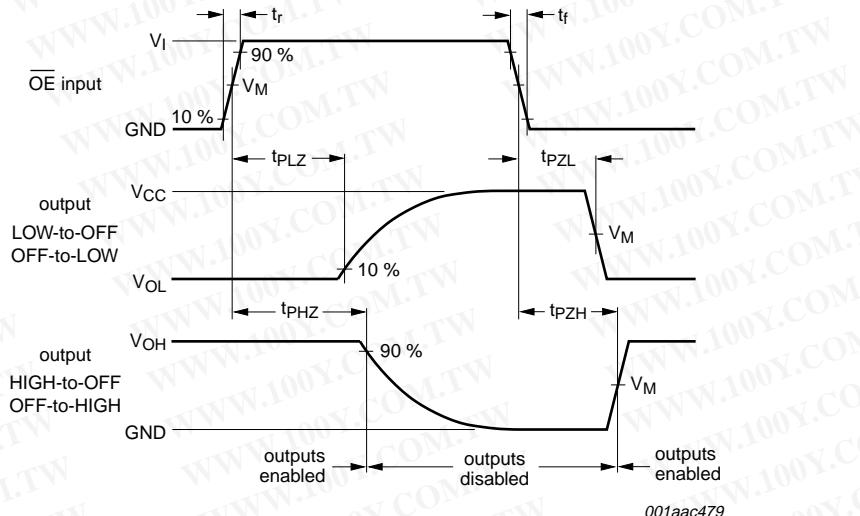
勝特力材料 886-3-5753170  
 勝特力電子(上海) 86-21-54151736  
 勝特力電子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)



Measurement points are given in [Table 11](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output drop that occur with the output load.

Fig 5. Input (An, Bn) to output (Bn, An) propagation delays and output transition times



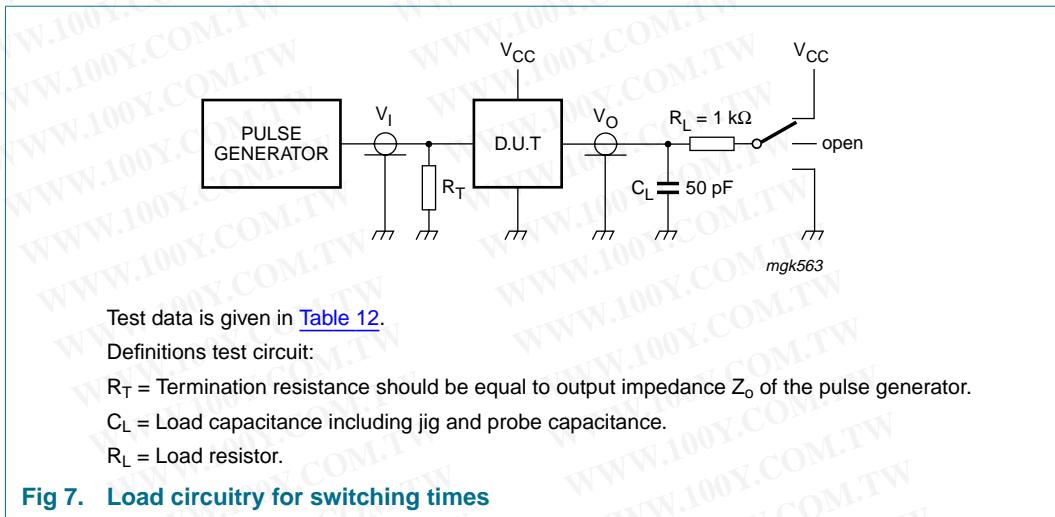
Measurement points are given in [Table 11](#).

$V_{OL}$  and  $V_{OH}$  are typical voltage output drop that occur with the output load.

Fig 6. 3-state output enable and disable times

Table 11: Measurement points

Type	Input	Output
	$V_M$	$V_M$
74HC245	$0.5V_{CC}$	$0.5V_{CC}$
74HCT245	1.3 V	1.3 V

**Table 12: Test data**

Type	Input		Test		
	$V_I$	$t_r, t_f$	$t_{PHL}, t_{PLH}$	$t_{PZH}, t_{PHZ}$	$t_{PZL}, t_{PLZ}$
74HC245	$V_{CC}$	6 ns	open	GND	$V_{CC}$
74HCT245	3 V	6 ns	open	GND	$V_{CC}$

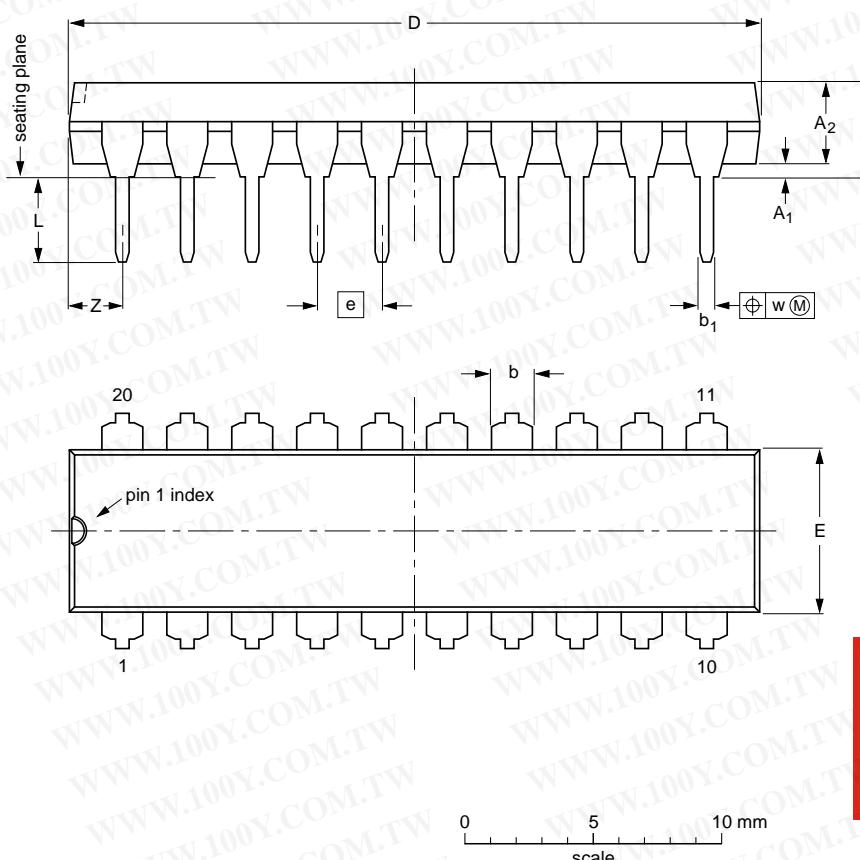
勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

## 13. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1



勝特力材料 886-3-5753170  
胜特力电子(上海) 86-21-54151736  
胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub> min.	A <sub>2</sub> max.	b	b <sub>1</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	e <sub>1</sub>	L	M <sub>E</sub>	M <sub>H</sub>	w	Z <sup>(1)</sup> max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	0.36 0.23	26.92 26.54	6.40 6.22	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.014 0.009	1.060 1.045	0.25 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.078

Note

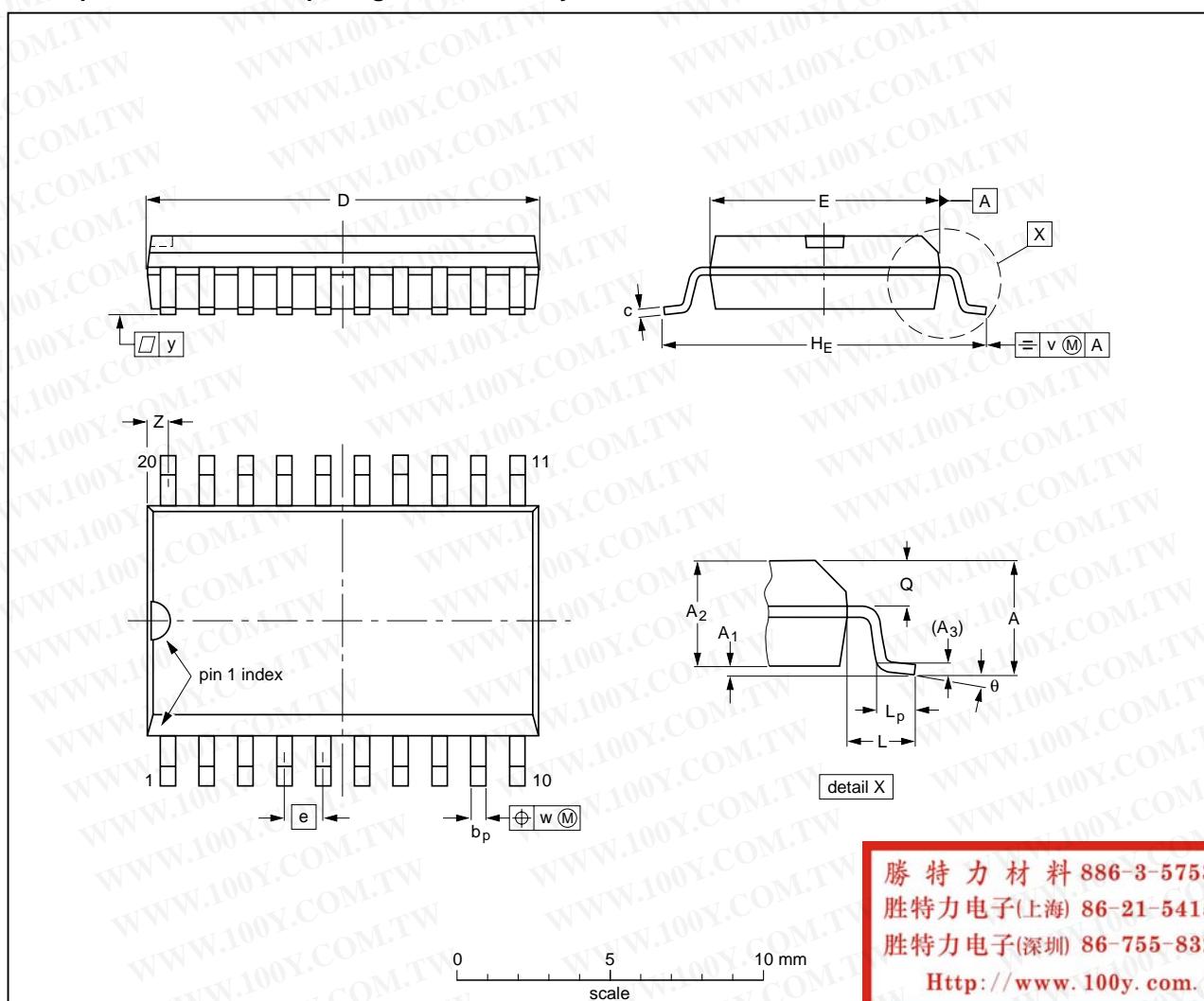
1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT146-1		MS-001	SC-603			99-12-27 03-02-13

Fig 8. Package outline SOT146-1 (DIP20)

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1



## DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(1)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	z <sup>(1)</sup>	θ
mm	2.65 0.1	0.3 2.25	2.45 0.25	0.25	0.49 0.36	0.32 0.23	13.0 12.6	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8° 0°
inches	0.1 0.004	0.012 0.089	0.096 0.014	0.01	0.019 0.014	0.013 0.009	0.51 0.49	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	

## Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT163-1	075E04	MS-013				-99-12-27 03-02-19

Fig 9. Package outline SOT163-1 (SO20)

勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-54151736  
 勝特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1

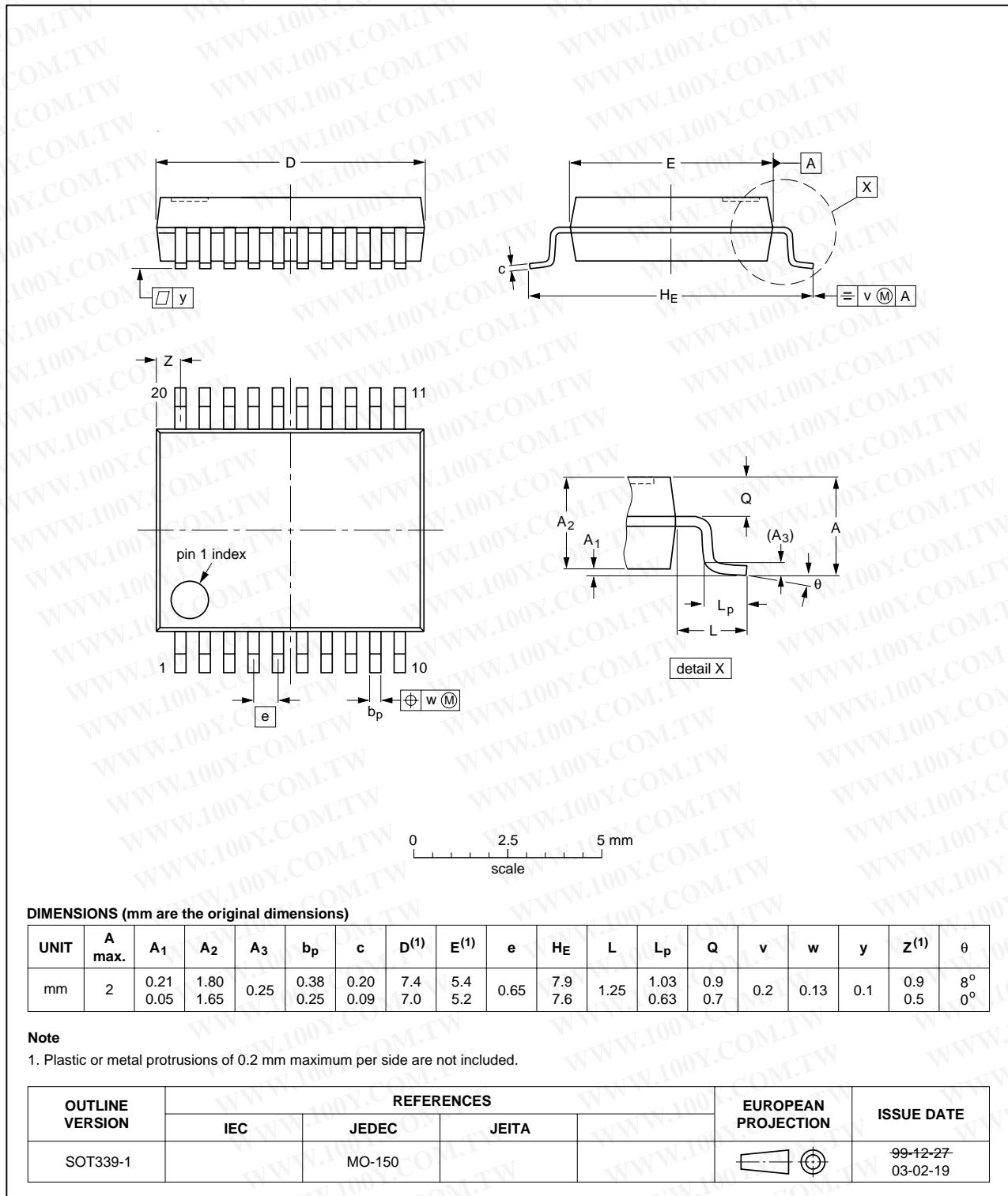
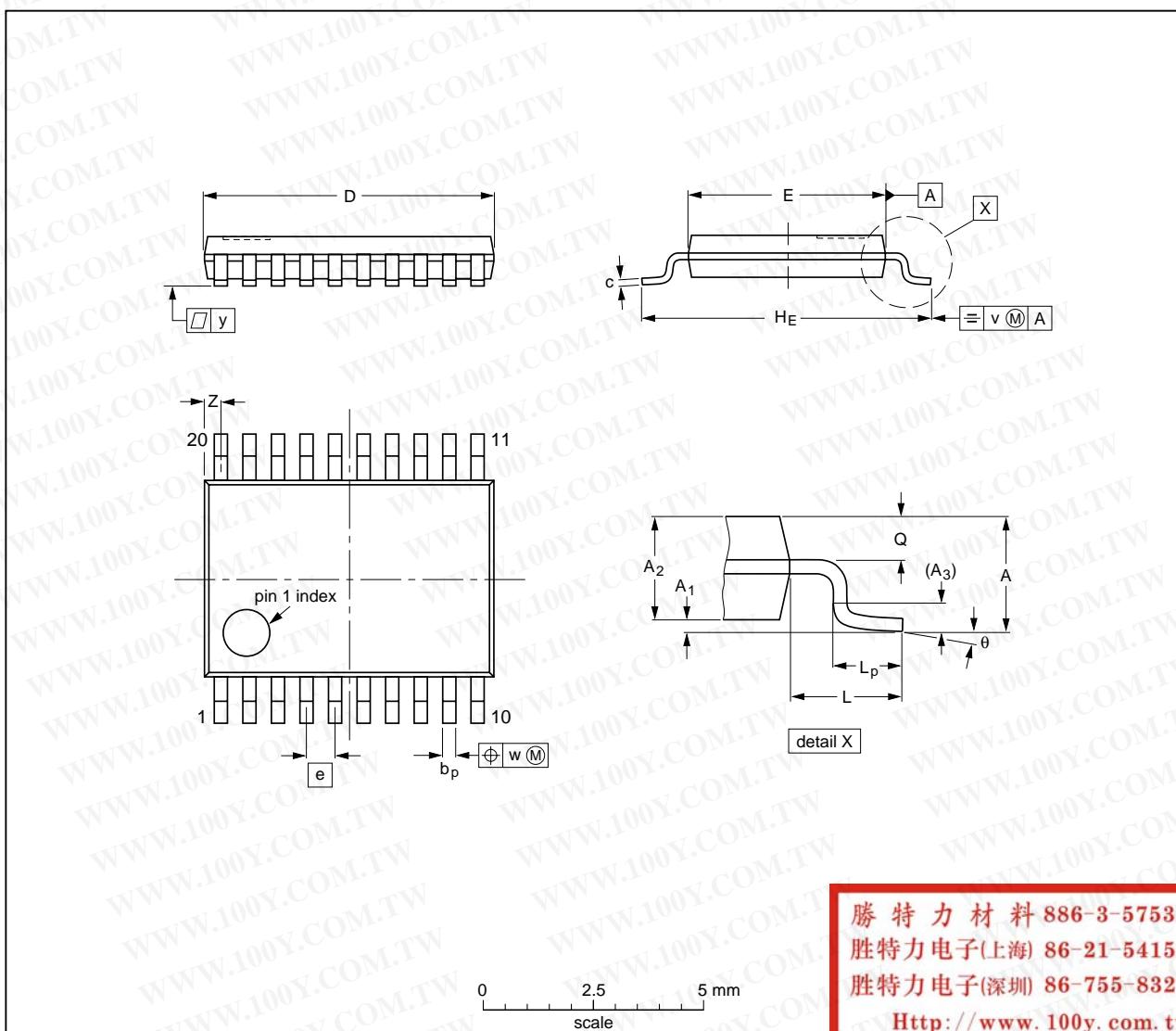


Fig 10. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1



## DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	A <sub>3</sub>	b <sub>p</sub>	c	D <sup>(1)</sup>	E <sup>(2)</sup>	e	H <sub>E</sub>	L	L <sub>p</sub>	Q	v	w	y	Z <sup>(1)</sup>	θ
mm	1.1 0.05	0.15 0.80	0.95	0.25	0.30 0.19	0.2 0.1	6.6 6.4	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

## Notes

- Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT360-1		MO-153				-99-12-27 03-02-19

Fig 11. Package outline SOT360-1 (TSSOP20)

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;  
 20 terminals; body 2.5 x 4.5 x 0.85 mm

SOT764-1

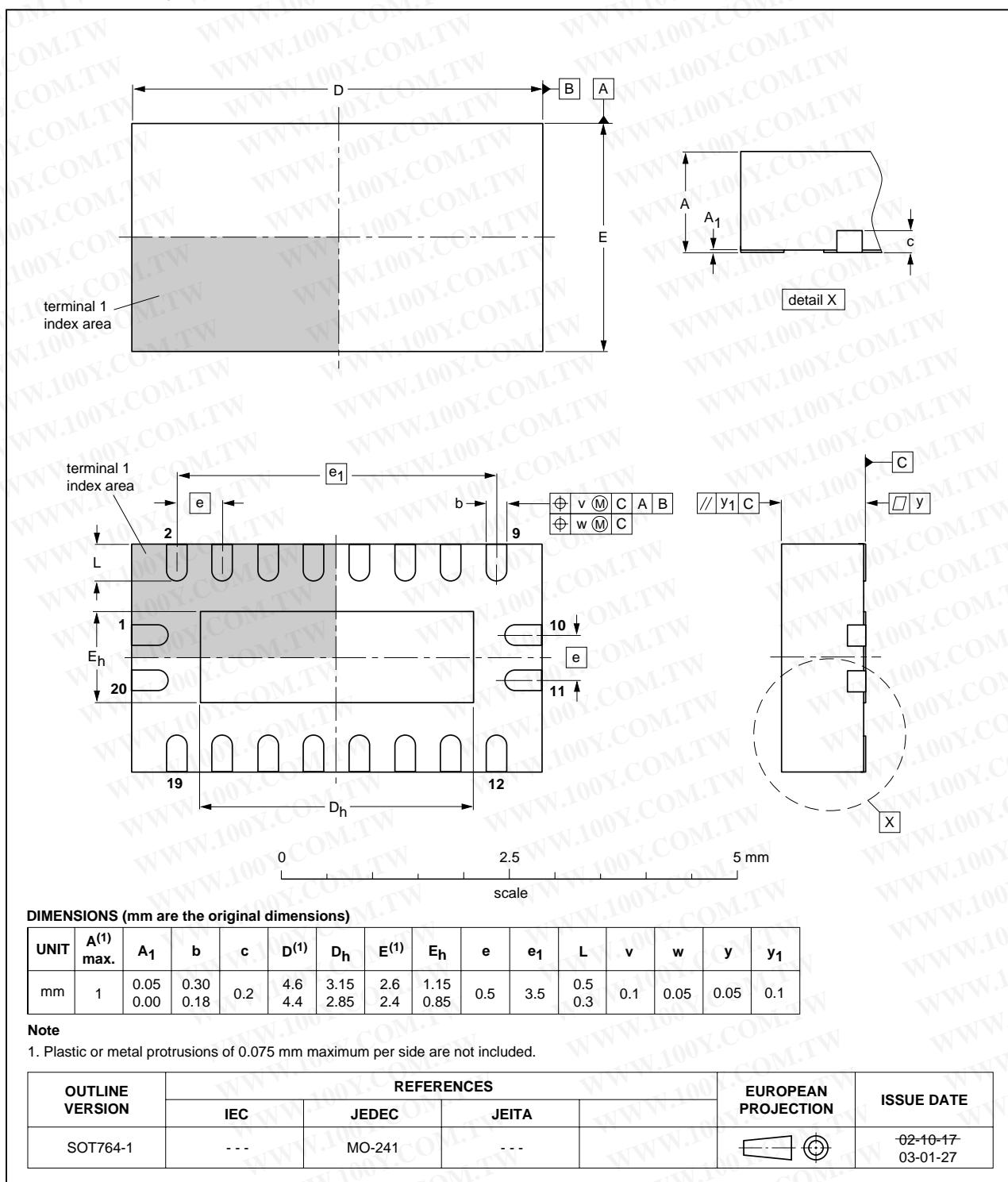


Fig 12. Package outline SOT764-1 (DHVQFN20)

## 14. Revision history

**Table 13: Revision history**

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74HC_HCT245_3	20050131	Product data sheet	-	9397 750 14502	74HC_HCT245_CNV_2
Modifications:			<ul style="list-style-type: none"> <li>• The format of this data sheet is redesigned to comply with the new presentation and information standard of Philips Semiconductors</li> <li>• <a href="#">Section 4 "Ordering information"</a>, <a href="#">Section 6 "Pinning information"</a> and <a href="#">Section 13 "Package outline"</a> are modified to include the DHVQFN20 package.</li> </ul>		
74HC_HCT245_CNV_2	19930930	Product specification	-	-	-

勝特力材料 886-3-5753170  
 胜特力电子(上海) 86-21-54151736  
 胜特力电子(深圳) 86-755-83298787  
[Http://www.100y.com.tw](http://www.100y.com.tw)

## 15. Data sheet status

Level	Data sheet status [1]	Product status [2][3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

## 16. Definitions

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Application information** — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

## 17. Disclaimers

**Life support** — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

**Right to make changes** — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

## 18. Contact information

For additional information, please visit: <http://www.semiconductors.philips.com>

For sales office addresses, send an email to: [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com)

勝特力材料 886-3-5753170  
胜特力电子(上海) 86-21-54151736  
胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

## 19. Contents

1	General description .....	1
2	Features .....	1
3	Quick reference data .....	1
4	Ordering information .....	2
5	Functional diagram .....	3
6	Pinning information .....	4
6.1	Pinning .....	4
6.2	Pin description .....	4
7	Functional description .....	5
7.1	Function table .....	5
8	Limiting values .....	5
9	Recommended operating conditions .....	6
10	Static characteristics .....	6
11	Dynamic characteristics .....	10
12	Waveforms .....	13
13	Package outline .....	15
14	Revision history .....	20
15	Data sheet status .....	21
16	Definitions .....	21
17	Disclaimers .....	21
18	Contact information .....	21

勝特力材料 886-3-5753170  
胜特力电子(上海) 86-21-54151736  
胜特力电子(深圳) 86-755-83298787

[Http://www.100y.com.tw](http://www.100y.com.tw)

© Koninklijke Philips Electronics N.V. 2005

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 31 January 2005  
Document number: 9397 750 14502

Published in The Netherlands

